## NSN 5961-01-211-8444

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View Online at https://aerobasegroup.com/nsn/5961-01-211-8444 **Inclosure Material:** Metal **Overall Length:** Between 0.970 inches and 1.218 inches Overall Diameter: 0.505 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-111 **Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.423 inches and 0.438 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 10.00 amperes source cutoff current and 30.00 nanoamperes base current, dc preset **Power Rating Per Characteristic:** 30.0 watts small-signal input power, common-collector absolute **Transfer Ratio:** 50.0 static forward current transfer ratio, common-emitter and 150.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** High power switching transistor; junction pattern arrangement: npn **Terminal Type And Quantity:** 2 uninsulated wire lead w/terminal lug and 1 wire hook Shelf Life: N/a **Unit Of Measure: Demilitarization:** 

Yes - demil/mli

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